

ME2187



High Efficiency, 10A Synchronous Boost Converter

General Description

ME2187 is a high power density synchronous boost converter which integrates two low $R_{\rm DS(ON)}$ MOSFETs to reduce conduction loss. It provides tiny and high efficiency solution for portable electronics. ME2187 has wide input voltage range from 2.7 to 12 V and can provide output voltage up to 12.6 V. It has 10 A switch current capability and is capable of delivering more than 30W power.

ME2187 uses current mode COT control to regulate output voltage. It works with PWM mode in moderate to heavy load. In light load, it can work with PFM mode and FPWM mode selected by the MODE pin to avoid problems caused by low switch frequency. The switch frequency is adjustable ranging from 200 kHz to 2.2 MHz by an external resistor. ME2187 is also capable of programming peak current limit and soft-start time. In addition, ME2187 provides UVLO, OVP and thermal shutdown protection.

Features

Input voltage range: 2.7 ~ 12 V

Output voltage range: 4.5 ~ 12.6 V

Low shutdown current: 1 ~ 3 uA

• Low R_{DS(ON)} MOSFETs (LSD/HSD): $13 \text{ m}\Omega / 16 \text{ m}\Omega$

• Up to 90% efficiency @ $V_{IN} = 3.3 \text{ V}$, $V_{OUT} = 9 \text{ V}$, and $I_{OUT} = 3 \text{ A}$

Adjustable switch frequency: 200 kHz ~ 2.2 MHz

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Selectable mode between PFM and FPWM

Programmable peak switch current limit

• Programmable soft-start time

Output over-voltage protection @ 13.4 V

Thermal shutdown @ 150 °C

Typical Applications

- Quick Charge Power Bank
- E-Cigarette
- Bluetooth Speaker
- Portable POS terminal

Package

- 16-pin ESOP16
- 20-pin DFN20L(4.5 x 3.5x0.9-0.5)
 DFN20L(4.5 x 3.5x0.75-0.5)



Typical Application Circuit

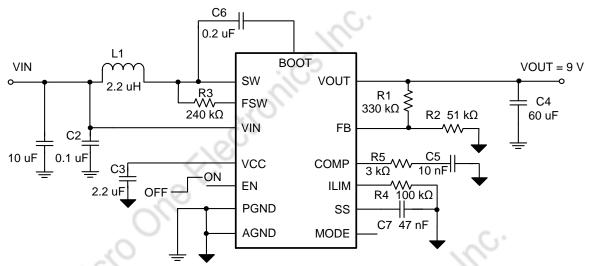
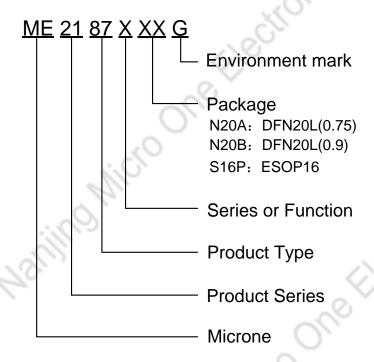


Fig 1. ME2187 typical application schematic

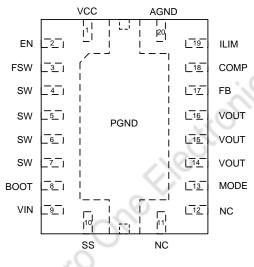
Selection Guide

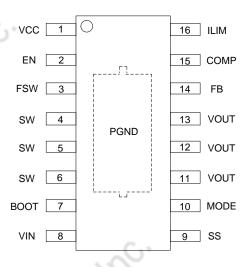


| product series | product description |
|----------------|-------------------------------------|
| ME2187AS16PG | Package: ESOP16 |
| ME2187AN20AG | Package: DFN20L(4.5 x 3.5x0.75-0.5) |
| ME2187AN20BG | Package: DFN20L(4.5 x 3.5x0.9-0.5) |



Pin Configuration





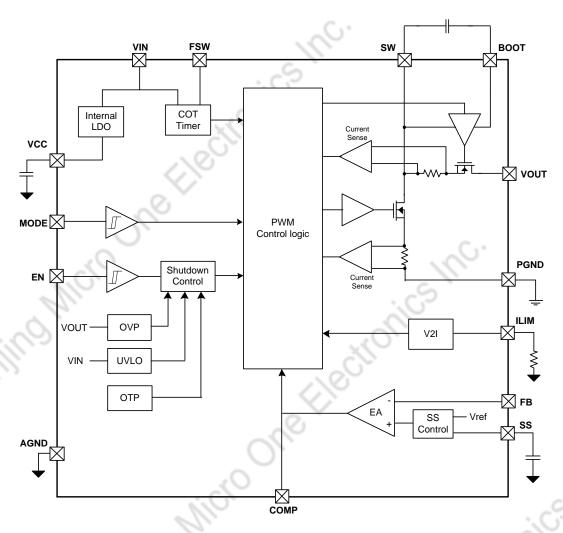
DFN20L ESOP16

Pin Assignment

| Pin | | | |
|------|------------------|------------------|--|
| Name | Number DFN20L | Number ESOP16 | Description |
| VCC | 1 | 1 | Output of internal LDO. A ceramic capacitor of more than 1 uF is required between VCC pin and ground. |
| EN | 2 | 2 | Enable logic input. Logic high enables IC and logic low disables IC. |
| FSW | 3 | 3 | Use external resistor between FSW pin and SW pin to set switch frequency |
| SW | 4, 5, 6, 7 | 4, 5, 6 | Switching node of boost converter. It is connected to the drain of LSD and the source of HSD. |
| воот | 8 | 7 | Power supply for HSD gate driver. A ceramic capacitor of more than 0.2 uF is required between BOOT pin and ground. |
| VIN | 9 | 8 | Power supply for IC. |
| SS | 10 | 9 | Use external capacitor between SS pin and ground to set soft-start time. |
| NC | 11, 12 | | No connection inside the IC. It's recommended to connect these two pins to ground to improve thermal performance. |
| MODE | 13 | 10 | Mode select pin. In light load, logic high or floating selects PFM mode and logic low selects FPWM mode. |
| VOUT | 14, 15, 16 | 11,12,13 | Output of boost converter. |
| FB | 17 | 14 | Voltage feedback. This pin is connected to the center tape of a resistor divider. |
| COMP | 18 | 15 | Output of internal error amplifier. Loop compensate network is required between COMP pin and ground. |
| ILIM | 19 | 16 | Use external resistor between ILIM pin and ground to set peak current limit. |
| AGND | 20 | | Analog ground. |
| PGND | Thermal PAD | Thermal PAD | Power ground. It is connected to the source of LSD. |



Block Diagram



Absolute Maximum Ratings (Note1)

| | Symb | ol | Description | Value | Unit |
|------------------|---------------|--------------|--|-----------------|------|
| | | BOOT | | -0.3 ~ SW + 6.6 | V |
| V_{PIN} | VIN, SV | V, FSW, VOUT | Voltage between each pin and | -0.3 ~ 14 | V |
| V PIN | | | ground. | -0.3 ~ 6.6 | V |
| T_A | | | Operating ambient temperature | -40 ~ 85 | οС |
| Τ _J | | | Operating junction temperature | -40 ~ 150 | οС |
| T _{stg} | | | Storage temperature | -55 ~150 | οС |
| T_lead | | | Lead temperature | 260 | °C |
| PD DFN20L ESOP16 | | DFN20L | Dower Dissipation | 2.4 | W |
| | | ESOP16 | Power Dissipation | 2.23 | W |
| DFN20L | | DFN20L | The state of the s | 52 | °C/W |
| E | Θ_{JA} | ESOP16 | Package thermal resistance | 56 | °C/W |
| | | | | | |

Note 1: Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device.



ESD Ratings

| Model | Value | Unit |
|--------------------------------------|-------|------|
| Human body mode(HBM), all pins | ±2000 | V |
| Charged device model (CDM), all pins | ±500 | V |

Recommended Operating Conditions

| Symbol | Description | Min | Тур | Max | Unit |
|----------------|-------------------------------------|-----|-----|------|------|
| V_{IN} | Input voltage range | 2.7 | - | 12 | V |
| V_{OUT} | Output voltage range | 4.5 | - | 12.6 | V |
| L | Inductance, effective value | 0.6 | 2.2 | 10 | uH |
| Co | Output capacitance, effective value | 10 | 60 | 1000 | uF |
| T _A | Operating ambient temperature | -40 | - | 85 | °C |

Electrical Characteristics

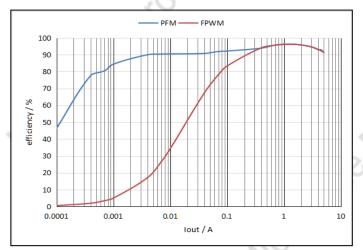
 $(T_A = 25 \, ^{\circ}\text{C}, \, V_{IN} = 3.6 \, \text{V}, \, V_{OUT} = 9 \, \text{V}, \, L = 2.2 \, \text{uH}, \, R_{ILIM} = 100 \, \text{k}\Omega, \, R_{FREQ} = 240 \, \text{k}\Omega, \, \text{unless otherwise specified})$

| Symbol | Description | Test Conditions | Min | Тур | Max | Unit |
|-----------------------|--|--|-------|-------|-------|------|
| V _{IN} | Input Voltage range | 200 | 2.7 | - | 12 | V |
| V _{UVLO} | Input UVLO threshold voltage | Input voltage rising | - | - | 2.7 | V |
| V _{UVLO_HYS} | UVLO hysteresis | <u> </u> | - | 0.2 | - | V |
| I _{SD} | Shutdown current into the VIN pin | IC disabled, no feedback resistor and load connected to VOUT pin | - | 1 | 3 | uA |
| IQ | Input quiescent current in PFM mode and empty load | IC enabled, no load, MODE pin floating | - | 600 | 1200 | uA |
| V _{CC} | Output voltage of internal LDO | V _{IN} = 8 V, I _{VCC} = 10 mA | 4 | 5 | 6 | V |
| V _{ENH} | EN logic high threshold voltage | VCC = 5 V | - | 9/1 | 1.2 | V |
| V _{ENH} | EN logic low threshold voltage | VCC = 5 V | 0.4 | O. | - | V |
| R _{EN} | EN internal pull-down resistor | VCC = 5 V | \C) | 800 | - | kΩ |
| V _{MODEH} | MODE logic high threshold voltage | VCC = 5 V | 100 | - | 4.0 | V |
| V _{MODEL} | MODE logic low threshold voltage | VCC = 5 V | 1.5 | - | - | V |
| R _{MODE} | MODE pull-up resistor | VCC = 5 V | - | 800 | - | kΩ |
| V _{OUT} | Output voltage range | 3.6 | 4.5 | - | 12.6 | V |
| V_{REF} | Feedback reference voltage | | 1.188 | 1.206 | 1.224 | V |
| I _{FB} | Leakage current into FB pin | V _{FB} = 1.5 V | - | - | 100 | nA |
| I _{SS} | Soft-start charging current | :1103 | - | 5 | - | uA |
| R _{DS(ON)1} | LSD on-resistance | . (1) | - | 13 | 17 | mΩ |
| R _{DS(ON)2} | HSD on-resistance | 7.0 | - | 16 | 21 | mΩ |
| I _{LIM_PFM} | Peak switch current limit in PFM mode | R_{ILIM} = 100 k Ω , MODE pin floating | - | 12.2 | - | А |



| I _{LIM_FPWM} | Peak switch current limit in FPWM mode | R_{ILIM} = 100 k Ω , MODE pin short to ground | - | 10.6 | - | А |
|-----------------------|--|--|---|------|-----|-----|
| F _{SW} | Switch frequency | R_{FREQ} = 240 k Ω , MODE pin short to ground | - | 550 | - | kHz |
| t _{min_ON} | Minimum on time | 10 | - | 110 | 200 | ns |
| t _{min_OFF} | Minimum off time | . 65 | - | 100 | 200 | ns |
| V _{OVP} | Output over-voltage protection threshold voltage | Output voltage rising | - | 13.4 | - | V |
| V _{OVP_HYS} | Output over-voltage protection hysteresis | | - | 0.3 | - | V |
| T _{SD} | Thermal shut down threshold | Junction temperature rising | - | 150 | - | °C |
| T _{SD_HYS} | Thermal shut down hysteresis | | - | 20 | - | °C |

Typical performance characteristics



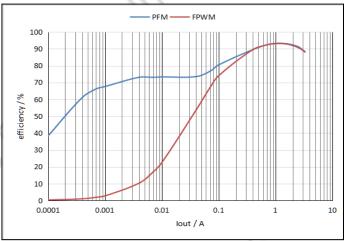
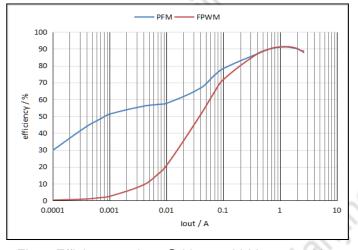
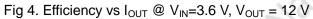


Fig 2. Efficiency vs I_{OUT} @ V_{IN} =3.6 V, V_{OUT} = 5 V

Fig 3. Efficiency vs I_{OUT} @ V_{IN} =3.6 V, V_{OUT} = 9 V





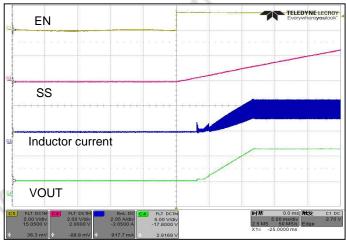


Fig 5. Start-up waveform

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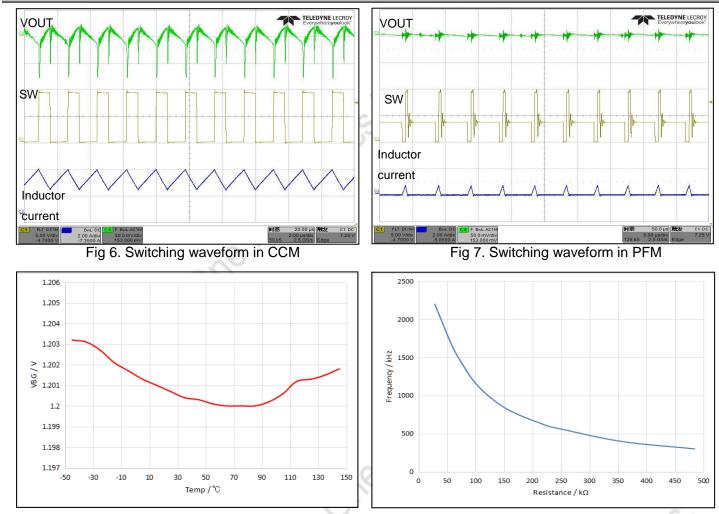


Fig 8. Reference voltage vs temperature

Fig 9. Switching frequency vs setting resistance

Operation Description

ME2187 is a synchronous boost converter which integrates two very low R_{DS(ON)} power switches to improve efficiency. It adopts current mode COT control topology to regulate output voltage. In moderate to heavy load, during every switching period, low-side MOSFET is turned on until switch current ramps up to a certain peak current determined by error amplifier. During dead time, inductor current flows through body diode of high-side MOSFET. After dead time, the high-side MOSFET is turned on and will be turned off after adaptive constant off time is reached. In light load, operating mode can be selected by MODE pin. When MODE pin is floating or logic high, ME2187 works in PFM mode and extends off time of switching period to reduce delivered energy. When MODE pin is short to ground, ME2187 works in FPWM mode. In FPWM mode, the power efficiency is low but the fixed switching frequency can avoid audible noise and other problems caused by low switching frequency.

Application Information

ME2187 is capable of providing 12.6 V output voltage. It integrates two internal 10A power switches and can deliver more than 30 W power. In light load, user can select PFM mode or FPWM mode by MODE pin. ME2187 also



supports programmable soft-start time, switching frequency and peak current limit.

Setting soft-start time

When EN pin is pulled up, soft-start capacitor C_{SS} between SS pin and ground is charged by a constant current of 5 uA. The lower of voltage on C_{SS} and internal feedback V_{REF} (1.206 V) is selected as reference input of error amplifier. FB pin voltage slowly ramps up with SS pin voltage. Soft-start phase is completed after SS pin voltage exceeds V_{REF} . When EN pin is pulled down, voltage on C_{SS} is discharged to ground. Soft-start time t_{SS} can be calculated by the following equation.

$$t_{SS} = \frac{V_{REF} \times C_{SS}}{I_{SS}}$$

Setting output voltage

The output voltage can be programmed by external resistor divider (R1 and R2 in typical application schematic) connected to VOUT pin. For reducing quiescent current in empty load, it is recommended to use large resistance between 10 k Ω and 1 M Ω for R1 and R2. The resistance of R1 can be calculated by following equation.

$$R_1 = \frac{(V_{OUT} - V_{REF}) \times R_2}{V_{REF}}$$

Setting switching frequency

The switching frequency can be programmed by external resistor R_{FREQ} between FSW pin and SW pin. The RFREQ required for desired frequency can be calculated using following equation.

$$R_{\text{FREQ}} = \frac{4 \times (\frac{1}{f_{\text{SW}}} - t_{\text{min_OFF}} \times \frac{V_{\text{OUT}}}{V_{\text{IN}}})}{C_{\text{FREQ}}}$$

Where V_{IN} is input voltage, V_{OUT} is output voltage, f_{SW} is switching frequency, C_{FREQ} is 25 pF, t_{min_OFF} is 100 ns

Setting peak current limit

The peak switch current limit can be set by external resistor R_{ILIM}. Please be advised that I_{LIM} in FPWM mode is 1.6A lower than that in PFM. To guarantee normal operation of boost converter, peak switch current limit should be higher than maximum inductor peak current. Peak current limit in PFM mode can be calculated using following equation.

$$I_{LIM} = \frac{1220000}{R_{ILIM}}$$

External component

1) High-side MOSFET driver is powered using external bootstrap capacitor. A ceramic capacitor of 200 nF

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should be connected between SW pin and BOOT pin.

- 2) The effective capacitance is decreased with DC bias. So it is necessary to leave margin to guarantee adequate effective capacitance especially for C_I and C_O.
- 3) When the inductor current approaches its saturation current, its inductance can decrease 30% from the value at 0-A current. The saturation current of used inductor should be higher than the maximum peak inductor current.

Board Layout Considerations

- 1) Boost converter implemented by ME2187 is sensitive to PCB layout. For reducing non-ideality, external component such as inductor, input capacitor, output capacitor, compensation network and resistor divider should be placed as nearly as possible to the chip.
- 2) For reducing EMI caused by high frequency switching, the trace connected to SW pin should be as short as possible. It is recommended to use ground plane to shield signal from interplane coupling.
- 3) To improve thermal dissipation and power efficiency, it is recommended to connect the thermal pad of package to ground plane. More thermal vias and thick PCB copper are desirable. Walilling Micro

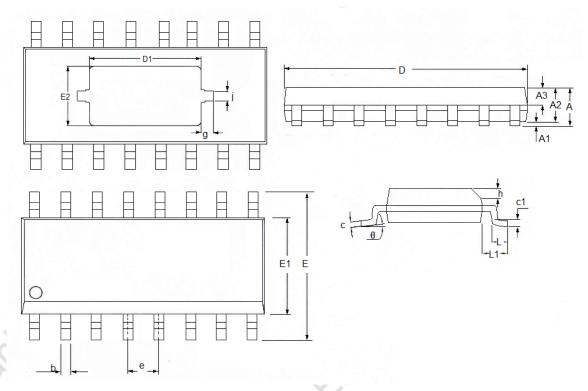
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Packaging Information

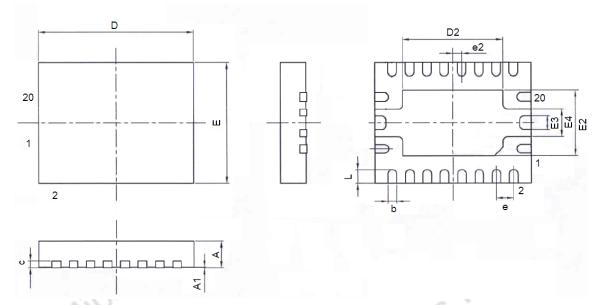
• Package Type: ESOP16



| DIM | Millimete | rs | Inch | nes | | |
|------------|-----------|-------|-----------|---------|--|--|
| DIM | Min | Max | Min | Max | | |
| А | 1.35 | 1.75 | 0.0531 | 0.0689 | | |
| A1 | 0.05 | 0.2 | 0.0020 | 0.0079 | | |
| A2 | 1.3 | 1.6 | 0.0512 | 0.0630 | | |
| A3 | 0.6 | 0.71 | 0.0236 | 0.0280 | | |
| b | 0.356 | 0.47 | 0.0140 | 0.0185 | | |
| С | 0.2 | 0.24 | 0.0079 | 0.0094 | | |
| D | 9.8 | 10.2 | 0.3858 | 0.4016 | | |
| E | 5.8 | 6.24 | 0.2283 | 0.2457 | | |
| E1 | 3.8 | 4 | 0.1496 | 0.1575 | | |
| е | 1.27BS0 | | 0.05 | 500 | | |
| h | 0.25 | 0.5 | 0.0098 | 0.0197 | | |
| L | 0.4 | 0.8 | 0.0157 | 0.0315 | | |
| L1 | 1.05BSC | | 0.04 | 113 | | |
| θ | 0 | 8° | 0 | 8° | | |
| c1 | 0.25 | :1100 | 0.0098 | | | |
| D1(95*180) | 4.57REF | | 0.1799REF | | | |
| E2(95*180) | 2.41REF | | 0.0949REF | | | |
| g | 0.51REF | | 0.021 | 0.02REF | | |
| j | 0.4REF | | 0.0157 | 7REF | | |



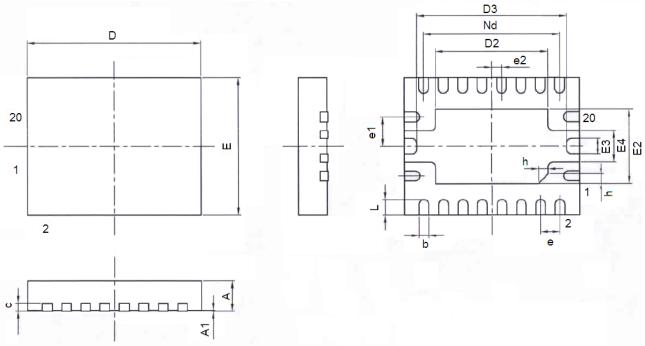
• Package Type: DFN20L(4.5 × 3.5×0.75-0.5)



| Min Max Min Max A 0.7 0.8 0.0275 0.0315 A1 0.05 0.0020 0.0020 b 0.2 0.3 0.0079 0.0118 c 0.203 0.0080 0.01772 D2 2.95 3.15 0.1161 0.1240 e 0.5(BSC) 0.0197(TYP) e2 0.25(BSC) 0.0098(BSC) E 3.5 0.1378 E2 1.95 2.15 0.0768 0.0846 E3 0.25 0.45 0.0098 0.0177 E4 0.65 0.85 0.0256 0.0335 L 0.3 0.5 0.0118 0.0197 | DIM | Millimet | ers | Inches | s |
|--|-----|----------|------|----------|--------|
| A1 0.05 0.0020 b 0.2 0.3 0.0079 0.0118 c 0.203 0.0080 D 4.5 0.1772 D2 2.95 3.15 0.1161 0.1240 e 0.5(BSC) 0.0197(TYP) e2 0.25(BSC) 0.0098(BSC) E 3.5 0.1378 E2 1.95 2.15 0.0768 0.0846 E3 0.25 0.45 0.0098 0.0177 E4 0.65 0.85 0.0256 0.0335 L 0.3 0.5 0.0118 0.0197 | DIM | Min | Max | Min | Max |
| b 0.2 0.3 0.0079 0.0118 c 0.203 0.0080 D 4.5 0.1772 D2 2.95 3.15 0.1161 0.1240 e 0.5(BSC) 0.0197(TYP) e2 0.25(BSC) 0.0098(BSC) E 3.5 0.1378 E2 1.95 2.15 0.0768 0.0846 E3 0.25 0.45 0.0098 0.0177 E4 0.65 0.85 0.0256 0.0335 L 0.3 0.5 0.0118 0.0197 | A | 0.7 | 0.8 | 0.0275 | 0.0315 |
| c 0.203 0.0080 D 4.5 0.1772 D2 2.95 3.15 0.1161 0.1240 e 0.5(BSC) 0.0197(TYP) e2 0.25(BSC) 0.0098(BSC) E 3.5 0.1378 E2 1.95 2.15 0.0768 0.0846 E3 0.25 0.45 0.0098 0.0177 E4 0.65 0.85 0.0256 0.0335 L 0.3 0.5 0.0118 0.0197 | A1 | 0 | 0.05 | CO | 0.0020 |
| D 4.5 0.1772 D2 2.95 3.15 0.1161 0.1240 e 0.5(BSC) 0.0197(TYP) e2 0.25(BSC) 0.0098(BSC) E 3.5 0.1378 E2 1.95 2.15 0.0768 0.0846 E3 0.25 0.45 0.0098 0.0177 E4 0.65 0.85 0.0256 0.0335 L 0.3 0.5 0.0118 0.0197 | b | 0.2 | 0.3 | 0.0079 | 0.0118 |
| D2 2.95 3.15 0.1161 0.1240 e 0.5(BSC) 0.0197(TYP) e2 0.25(BSC) 0.0098(BSC) E 3.5 0.1378 E2 1.95 2.15 0.0768 0.0846 E3 0.25 0.45 0.0098 0.0177 E4 0.65 0.85 0.0256 0.0335 L 0.3 0.5 0.0118 0.0197 | С | 0.203 | 0. | 0.0080 | 0 |
| e 0.5(BSC) 0.0197(TYP) e2 0.25(BSC) 0.0098(BSC) E 3.5 0.1378 E2 1.95 2.15 0.0768 0.0846 E3 0.25 0.45 0.0098 0.0177 E4 0.65 0.85 0.0256 0.0335 L 0.3 0.5 0.0118 0.0197 | D | 4.5 | 200 | 0.1772 | 2 |
| e2 0.25(BSC) 0.0098(BSC) E 3.5 0.1378 E2 1.95 2.15 0.0768 0.0846 E3 0.25 0.45 0.0098 0.0177 E4 0.65 0.85 0.0256 0.0335 L 0.3 0.5 0.0118 0.0197 | D2 | 2.95 | 3.15 | 0.1161 | 0.1240 |
| E 3.5 0.1378 E2 1.95 2.15 0.0768 0.0846 E3 0.25 0.45 0.0098 0.0177 E4 0.65 0.85 0.0256 0.0335 L 0.3 0.5 0.0118 0.0197 | е | 0.5(BS | C) | 0.0197(T | YP) |
| E2 1.95 2.15 0.0768 0.0846 E3 0.25 0.45 0.0098 0.0177 E4 0.65 0.85 0.0256 0.0335 L 0.3 0.5 0.0118 0.0197 | e2 | 0.25(BS | SC) | 0.0098(B | SC) |
| E3 0.25 0.45 0.0098 0.0177 E4 0.65 0.85 0.0256 0.0335 L 0.3 0.5 0.0118 0.0197 | E | 3.5 | AL. | 0.1378 | 3 |
| E4 0.65 0.85 0.0256 0.0335 L 0.3 0.5 0.0118 0.0197 | E2 | 1.95 | 2.15 | 0.0768 | 0.0846 |
| L 0.3 0.5 0.0118 0.0197 | E3 | 0.25 | 0.45 | 0.0098 | 0.0177 |
| C. Y | E4 | 0.65 | 0.85 | 0.0256 | 0.0335 |
| arijing Micro One | L | 0.3 | 0.5 | 0.0118 | 0.0197 |
| | | | | Mickoou | |



• Package Type: DFN20L(4.5 × 3.5×0.9-0.5)



| DIM 33 | Millimeters | | Inch | nes | |
|--------|-------------|-------|-------------|-------------|--|
| DIM | Min | Max | Min | Max | |
| Α | 0.85 | 0.95 | 0.0335 | 0.0374 | |
| A1 | | 0.05 | V. | 0.0020 | |
| b | 0.18 | 0.3 | 0.0071 | 0.0118 | |
| С | 0.18 | 0.25 | 0.0071 | 0.0098 | |
| D | 4.4 | 4.6 | 0.1732 | 0.1811 | |
| D2 | 3.1 | 3.3 | 0.1220 | 0.1299 | |
| D3 | 3.85 | (REF) | 0.1516 | SREF | |
| е | 0.5(| BSC) | 0.0197 | (TYP) | |
| e1 | 0.75 | (BSC) | 0.0295 | (BSC) | |
| e2 | 0.25(BSC) | | 0.0098 | (BSC) | |
| Nd | 3.5(| BSC) | 0.1378 | 0.1378(BSC) | |
| E | 3.4 | 3.6 | 0.1339 | 0.1417 | |
| E2 | 2.1 | 2.3 | 0.0827 | 0.0906 | |
| E3 | 0.35(BSC) | | 0.0138(BSC) | | |
| E4 | 0.75(BSC) | | 0.0295(BSC) | | |
| L | 0.35 | 0.45 | 0.0138 | 0.0177 | |
| h | 0.2 | 0.3 | 0.0079 | 0.0118 | |



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